

S62	14608	((438/96) or (438/97) or (438/149) or (438/150) or (438/151) or (438/166) or (438/299) or (438/308) or (438/364) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/491) or (438/585) or (438/694) or (438/710) or (438/795) or (438/913)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/02 21:44
S63	5	S62 and (((gate near2 (dielectric or insulat\$3)) near5 (anneal\$3 or heat\$3)) same (vacuum or (below near2 ("atm" or atmospheric) near2 pressure))))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/02 21:51
S64	9677	((438/149) or (438/151) or (438/164) or (438/166) or (438/479) or (438/482) or (438/485) or (438/486) or (438/487) or (438/488) or (438/491) or (438/758) or (438/778) or (438/787)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/16 17:57
S65	101	S64 and (vacuum near10 ("SiO" or (silicon adj oxide)) or (gate adj (insulat\$3 or passivat\$3 or dielectric))))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/16 18:06
S66	43	S64 and (vacuum near10 ("SiO" or (silicon adj oxide)) or (gate adj (insulat\$3 or passivat\$3 or dielectric))) near10 deposit\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/16 18:07
S67	3	S64 and (vacuum near10 ("SiO" or (silicon adj oxide)) or (gate adj (insulat\$3 or passivat\$3 or dielectric))) near10 deposit\$3 near10 (anneal\$3 or heat\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/16 18:08
S68	106	(vacuum near10 ("SiO" or (silicon adj oxide)) or (gate adj (insulat\$3 or passivat\$3 or dielectric))) near10 deposit\$3 near10 (anneal\$3 or heat\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/16 18:26

S69	101	deposit\$3 near10 vacuum near10 (anneal\$3 or heat\$3) near10 ("SiO" or (silicon adj oxide))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/16 18:28
S70	15	S69 not S68	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/16 18:29
S71	1297	(438/151).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/19 14:48
S72	902	(438/758).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/19 16:30
S73	1387	(438/778).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/19 18:36
S74	817	(438/787).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/19 17:51
S75	1109	(438/488).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/19 15:33
S76	1062	(438/166).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/19 19:06

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1548	(438/149).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/19 19:09
S1	12368	((438/96) or (438/97) or (438/149) or (438/150) or (438/151) or (438/166) or (438/299) or (438/308) or (438/364) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/491) or (438/585) or (438/694) or (438/710) or (438/795) or (438/913)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/02 21:44
S2	0	((gate near3 insulat\$4) same (anneal\$3 or heat\$3)) near5 vacuum	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/27 19:15
S3	0	((sio or (silicon near2 oxide)) same (anneal\$3 or heat\$3)) near5 vacuum	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/16 14:15
S4	0	((sio or (silicon near2 oxide)) and (anneal\$3 or heat\$3)) near5 vacuum	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/15 22:01
S5	12368	((438/96) or (438/97) or (438/149) or (438/150) or (438/151) or (438/166) or (438/299) or (438/308) or (438/364) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/491) or (438/585) or (438/694) or (438/710) or (438/795) or (438/913)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/07/16 14:13
S6	112	((sio or (silicon near2 oxide)) same (anneal\$3 or heat\$3)) near5 vacuum	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/16 14:17

S7	6	((gate near3 insulat\$4) same (anneal\$3 or heat\$3)) near5 vacuum	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/16 14:15
S8	5	((((438/96) or (438/97) or (438/149) or (438/150) or (438/151) or (438/166) or (438/299) or (438/308) or (438/364) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/491) or (438/585) or (438/694) or (438/710) or (438/795) or (438/913)).CCLS.) and (((sio or (silicon near2 oxide)) same (anneal\$3 or heat\$3)) near5 vacuum)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/16 14:19
S9	1353	(poly near2 crystall\$8) same (poly near2 silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/16 16:32
S10	455320	tft or (thin near2 film)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/16 14:21
S11	275	((poly near2 crystall\$8) same (poly near2 silicon)) same (tft or (thin near2 film))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/14 17:49
S12	291495	(anneal\$3 or heat\$3) same (vacuum or (low near2 pressure))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/16 14:29
S13	275	((poly near2 crystall\$8) same (poly near2 silicon)) same (tft or (thin near2 film))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/16 14:38
S14	54	((((poly near2 crystall\$8) same (poly near2 silicon)) same (tft or (thin near2 film)))) and ((anneal\$3 or heat\$3) same (vacuum or (low near2 pressure)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/16 14:24

S15	249811	(anneal\$3 or heat\$3) same (vacuum)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/16 14:36
S16	27	((poly near2 crystall\$8) same (poly near2 silicon)) same (tft or (thin near2 film))) and ((anneal\$3 or heat\$3) same (vacuum))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/16 14:30
S17	58093	(anneal\$3 or heat\$3) near3 (vacuum)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/16 14:39
S18	10	((poly near2 crystall\$8) same (poly near2 silicon)) same (tft or (thin near2 film))) and ((anneal\$3 or heat\$3) near3 (vacuum))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/16 14:37
S19	605	((poly near2 crystall\$8) same (poly near2 silicon)) and (tft or (thin near2 film))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/16 14:38
S20	5134	((anneal\$3 or heat\$3) near3 (vacuum)) same insulat\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/16 14:50
S21	2991	((anneal\$3 or heat\$3) near3 (vacuum)) near5 insulat\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/16 14:51
S22	1	((anneal\$3 or heat\$3) near3 (vacuum)) near5 insulat\$3) and (((poly near2 crystall\$8) same (poly near2 silicon)) and (tft or (thin near2 film)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/16 14:50
S23	9	((anneal\$3 or heat\$3) near3 (vacuum)) near5 (gate near3 insulat\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/16 14:51
S24	3613	(anneal\$3 or heat\$3) near4 (insulat\$3 or (gate near2 insulat\$3)) near4 vacuum	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/16 16:32

S25	1353	(poly near2 crystall\$8) same (poly near2 silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/16 16:32
S26	2	((anneal\$3 or heat\$3) near4 (insulat\$3 or (gate near2 insulat\$3)) near4 vacuum) and ((poly near2 crystall\$8) same (poly near2 silicon))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/16 16:33
S27	12423	((438/96) or (438/97) or (438/149) or (438/150) or (438/151) or (438/166) or (438/299) or (438/308) or (438/364) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/491) or (438/585) or (438/694) or (438/710) or (438/795) or (438/913)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/07/27 19:15
S28	2538	((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/28 23:20
S29	412	((((438/96) or (438/97) or (438/149) or (438/150) or (438/151) or (438/166) or (438/299) or (438/308) or (438/364) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/491) or (438/585) or (438/694) or (438/710) or (438/795) or (438/913)).CCLS.) and (((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/27 19:17
S30	124905	vacuum near5 chamber	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/27 19:18
S31	12653	fns or ((fowler adj Nordheim) near2 stress)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/28 23:17

S32	69	(((438/96) or (438/97) or (438/149) or (438/150) or (438/151) or (438/166) or (438/299) or (438/308) or (438/364) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/491) or (438/585) or (438/694) or (438/710) or (438/795) or (438/913)).CCLS.) and (((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3))) and (vacuum near5 chamber)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/27 19:19
S33	1	(((438/96) or (438/97) or (438/149) or (438/150) or (438/151) or (438/166) or (438/299) or (438/308) or (438/364) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/491) or (438/585) or (438/694) or (438/710) or (438/795) or (438/913)).CCLS.) and (((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3))) and (vacuum near5 chamber)) and (fns or ((fowler adj Nordheim) near2 stress))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/27 19:19
S34	3	(((438/96) or (438/97) or (438/149) or (438/150) or (438/151) or (438/166) or (438/299) or (438/308) or (438/364) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/491) or (438/585) or (438/694) or (438/710) or (438/795) or (438/913)).CCLS.) and (((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3))) and (fns or ((fowler adj Nordheim) near2 stress))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/27 19:20
S35	212	(((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3)) and (vacuum near5 chamber)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 15:15

S36	3	(((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3)) and (vacuum near5 chamber)) and (fns or ((fowler adj Nordheim) near2 stress))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/27 19:21
S37	0	"6638876".URPN.	USPAT	OR	OFF	2004/07/27 19:23
S38	24	("4585492" "5210056" "5578848" "5880040" "6020024" "6121130" "6136725" "6165834" "6168980" "6177363" "6191011" "6258690" "6274454" "6287897" "6291867" "6300203" "6306742" "6326231" "6326258" "6333557" "6335049" "6337289" "6338996" "6451713").PN.	USPAT	OR	OFF	2004/07/27 19:23
S39	3	(((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3)) and (fns or ((fowler adj Nordheim) near2 stress))) and (((438/96) or (438/97) or (438/149) or (438/150) or (438/151) or (438/166) or (438/299) or (438/308) or (438/364) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/491) or (438/585) or (438/694) or (438/710) or (438/795) or (438/913)).CCLS.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/27 19:25
S40	4	(((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3)) and (fns or ((fowler adj Nordheim) near2 stress))) and vacuum	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/27 19:26
S41	39	(((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3)) and (fns or ((fowler adj Nordheim) near2 stress))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/27 20:08
S42	211701	sio or (silicon near2 oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/27 20:08
S43	29	(((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3)) and (fns or ((fowler adj Nordheim) near2 stress))) and (sio or (silicon near2 oxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/27 20:08

S44	529	((gate near5 (dielectric or insulat\$3 or oxide)) same (sio or (silicon near2 oxide)) near10 anneal\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/27 20:24
S45	50	(fns or (fowler adj Nordheim)) near2 stress	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/27 20:25
S46	1	(((((gate near5 (dielectric or insulat\$3 or oxide)) same (sio or (silicon near2 oxide)) near10 anneal\$3)) and vacuum) and (fns or ((fowler adj Nordheim) near2 stress)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/27 20:26
S47	13	(((((gate near5 (dielectric or insulat\$3 or oxide)) same (sio or (silicon near2 oxide)) near10 anneal\$3)) and (fns or ((fowler adj Nordheim) near2 stress)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/27 20:30
S48	132	(((((gate near5 (dielectric or insulat\$3 or oxide)) same (sio or (silicon near2 oxide)) near10 anneal\$3)) and vacuum	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/27 20:40
S49	12653	fns or ((fowler adj Nordheim) near2 stress)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/28 23:17
S50	2538	((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/28 23:20
S51	4	(fns or ((fowler adj Nordheim) near2 stress)) same (((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/28 23:21
S52	0	(fns or ((fowler adj Nordheim) near2 stress)) near5 (((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/28 23:21
S53	2	(fns or ((fowler adj Nordheim) near2 stress)) near10 (((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/28 23:21

S54	13414	((438/96) or (438/97) or (438/149) or (438/150) or (438/151) or (438/166) or (438/299) or (438/308) or (438/364) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/491) or (438/585) or (438/694) or (438/710) or (438/795) or (438/913)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/14 17:48
S55	103	S54 and (anneal\$3 near4 (gate near2 insulat\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/14 17:50
S56	44	S55 and vacuum	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/14 17:50
S57	26	"6168980"	USPAT	OR	OFF	2005/06/07 13:08
S58	1	("6168980").PN.	USPAT	OR	OFF	2005/06/07 13:08
S59	14087	((438/96) or (438/97) or (438/149) or (438/150) or (438/151) or (438/166) or (438/299) or (438/308) or (438/364) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/491) or (438/585) or (438/694) or (438/710) or (438/795) or (438/913)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/07 15:14
S60	74	S59 and (((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3)) and (vacuum near5 chamber)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 15:16
S61	40	S60 and ((h2 or hydrogen) near5 atmosphere)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 15:16